

	Type	Hits	Search Text	DBs
78	BRS	3	(deposit\$4 with conductive with (metal or metallic or material) with situ) same (electroplat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
79	BRS	4	(deposit\$4 with conductive with (metal or metallic or material) with situ) and 205/\$.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
80	BRS	26	(plating near2 bias) with (substrate or surface or semiconductor) same (electroplat\$4 or electrochemical)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
81	BRS	565	(conductive) near3 (material or metal or metallic) with situ	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
82	BRS	47	(conductive) near3 (material or metal or metallic) with situ same (electroplat\$4 or electrochemic\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
83	BRS	108	(conductive) near3 (material or metal or metallic) with situ with (deposit\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
84	BRS	1	(trench or via or hole or open\$4) with (situ) with (electrochemical) with deposit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
85	BRS	52	(situ) with (electrochemical) with deposit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
86	BRS	4	((conductive) near3 (material or metal or metallic) with situ with (deposit\$4)) and 205/\$.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
87	BRS	38	(conductive) near3 (material or metal or metallic) with situ with (deposit\$4) same (semiconductor or trench or open\$4 or via\$4 or hole\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
88	BRS	1	((conductive) near3 (material or metal or metallic) with situ with (deposit\$4) same (semiconductor or trench or open\$4 or via\$4 or hole\$4)) and 205/\$.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
89	BRS	19	((conductive) near3 (material or metal or metallic) with situ) and 205/\$.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
90	BRS	0	6423636.pn. and situ	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
91	BRS	4	"6423636"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
92	BRS	0	6423636.pn. and bath and bias and plating\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
93	BRS	0	6423636.pn. and bath and bias	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
94	BRS	0	6423636.pn. and bath	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
95	BRS	3	"6423636" and (bath or bias or electrochemical)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
96	BRS	3	("6423636" and (bath or bias or electrochemical)) and bias	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
97	BRS	2	6423636.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
98	BRS	2	6423636.pn. and bias\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
99	BRS	0	6423636.pn. and pulse	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
100	BRS	1	6423636.pn. and volt\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
101	BRS	1	6423636.pn. and second\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
102	BRS	2	6423636.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
103	BRS	1	6423636.pn. and (volt\$4 or voltage\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
104	BRS	0	6423636.pn. and (puls\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
105	BRS	92	(pulse near2 plat\$4) with electroplat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
106	BRS	21	((pulse near2 plat\$4) with electroplat\$4 ) same (semiconductor or DRAM or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
107	BRS	0	(complex near2 wave) with electroplat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
108	BRS	7	((complex near2 wave) with electric\$4) and (electroplat\$4 or electrochemical or electrolysis)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
109	BRS	151	(complex near2 wave) with electric\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
110	BRS	4	((complex near2 wave) with electric\$4) with energy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
111	BRS	3	(electric\$4 near3 energy) with (complex near2 wave)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
112	BRS	16	(205/\$.ccls. or 204/\$.ccls.) and (complex near2 wave)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
113	BRS	1	"99047731"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
114	BRS	23	chen and linlin and semitool	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
115	BRS	0	"990545527"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
116	BRS	0	"99545527"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
117	BRS	0	"99/545527"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
118	BRS	0	"wo 99/545527"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
119	BRS	0	"wo 99545527"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
120	BRS	2	6113771.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
121	BRS	1	"99054527"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
122	BRS	4	"9954527"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
123	BRS	3	"2002063064"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
124	BRS	2	"20020063064"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB